

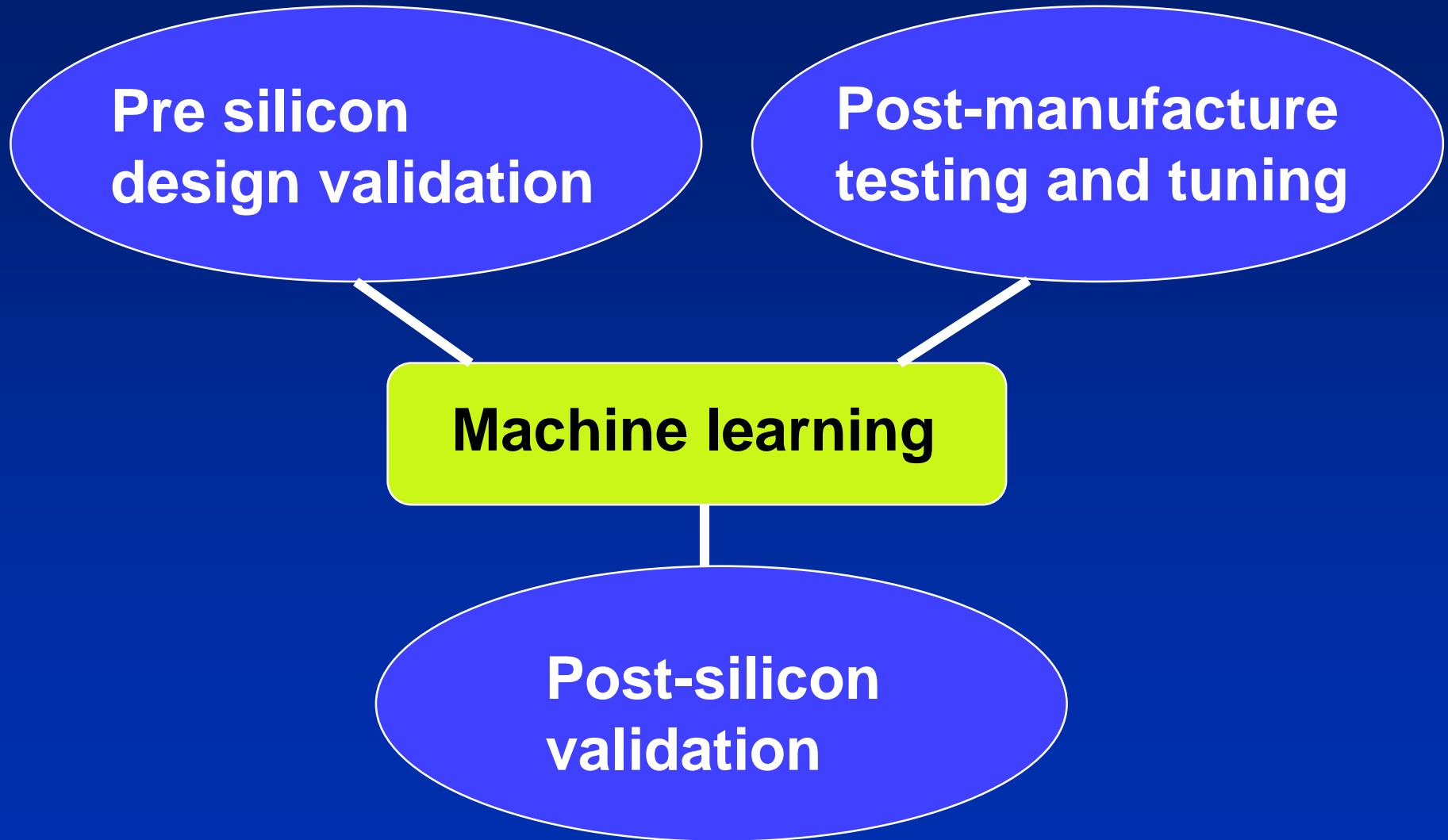
**VALIDATION, TESTING AND TUNING OF MIXED-SIGNAL/RF
CIRCUITS AND SYSTEMS:
A MACHINE LEARNING ASSISTED APPROACH**

*A. Chatterjee,
Georgia Tech*

*GRAs: S. Deyati, B. Muldrey, S.Akbay, V. Natarajan, R.
Senguttuvan, S. Sen, R. Voorakaranam, S. Cherubal, P. Variyam,
S. Chakrabarti, D. Han and X. Wang*

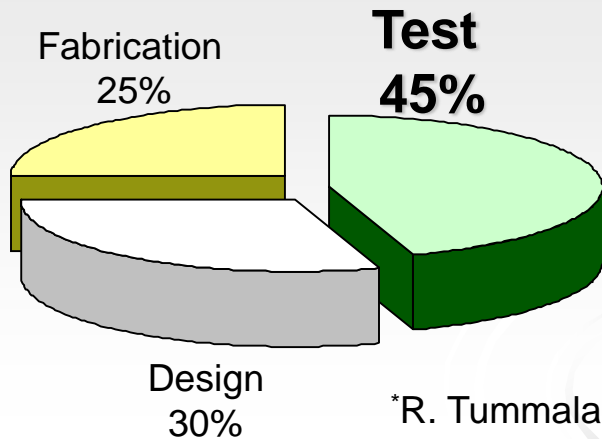
Ack: SRC, Intel Corp, NSF and MARCO-DARPA

Background: Mixed-Signal/RF Systems



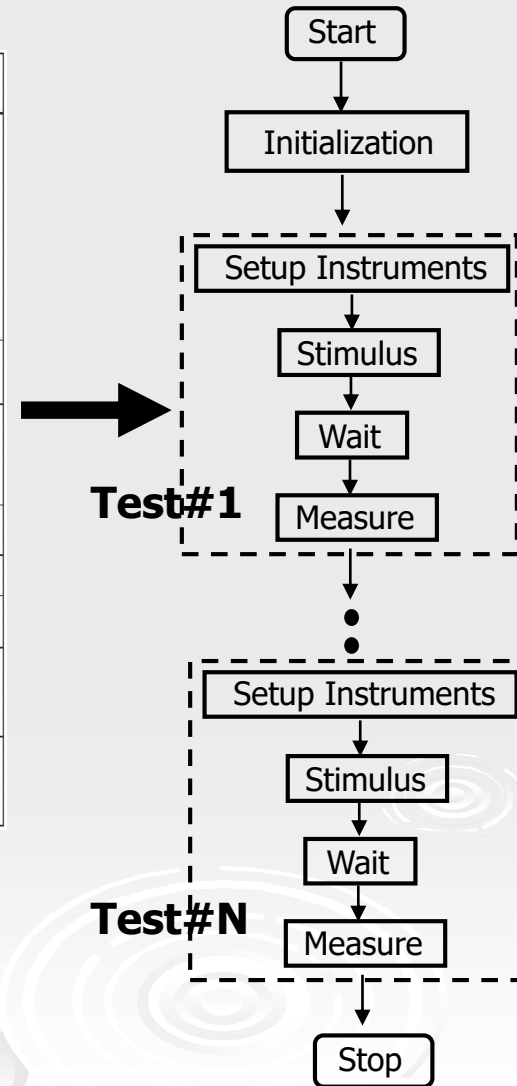
State of the Art in Test: Mixed-Signal SoCs

- Specification Tests
- Each test requires a different setup
 - Total testing time
 - ATE complexity
 - Load board complexity
- Test cost up 30%- 45%*



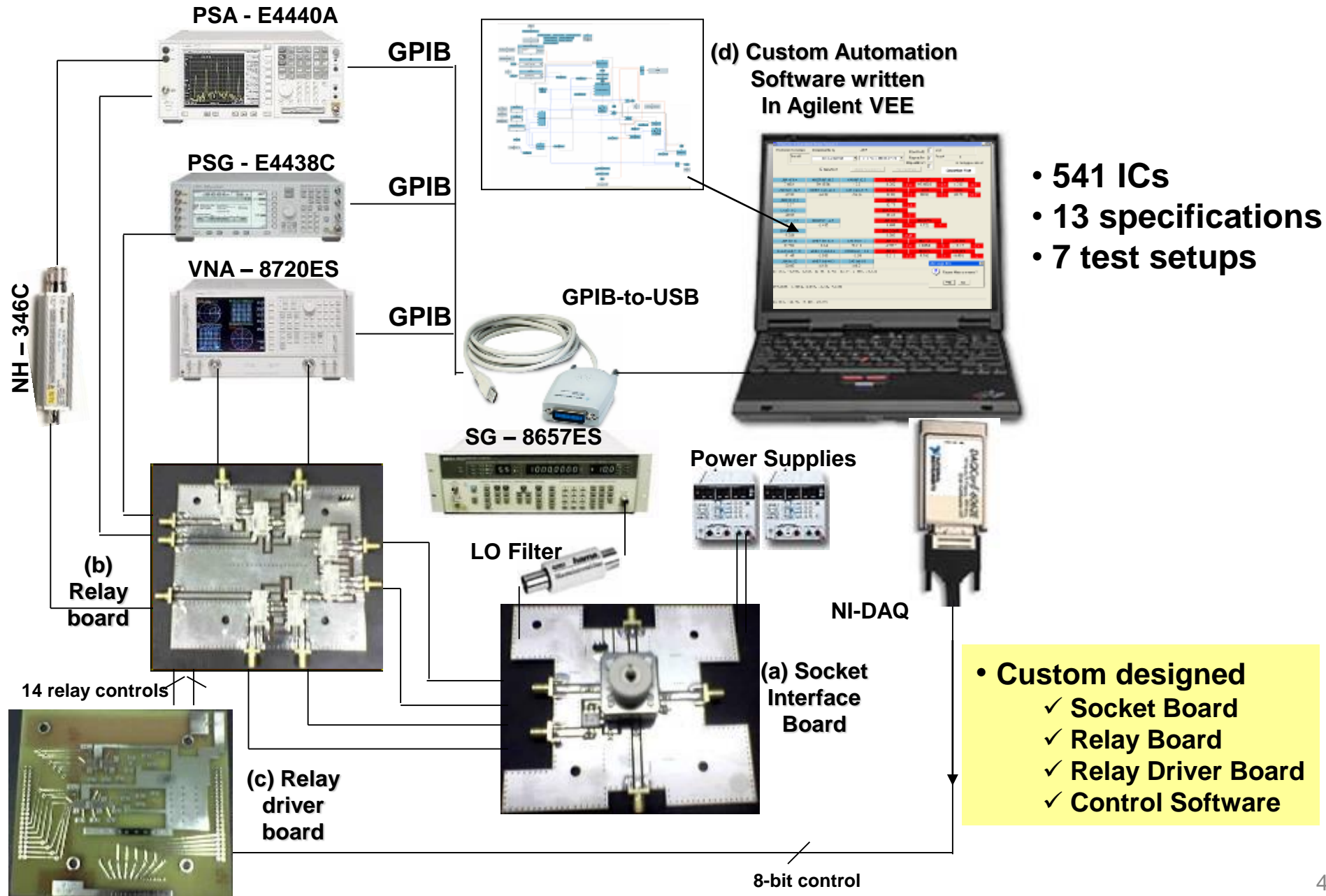
PARAMETER	CONDITION	OPA277P, U OPA277P, U			OPA277PA, UA OPA277PA, UA			UNITS
		MIN	TYP ¹	MAX	MIN	TYP ¹	MAX	
Offset Input Offset Voltage (single) OPA277P, U (high grade, full) All PA, UA Versions	V_{OS}		±10	±20			±50	μV
	Input Offset Voltage Over Temperature OPA277P, U (high grade, single) OPA277P, U (high grade, full) All PA, UA Versions	$T_A = -40^\circ\text{C to }+85^\circ\text{C}$		±50			±100	μV
	Input Offset Voltage Drift OPA277P, U (high grade, single) OPA277P, U (high grade, full) All PA, UA Versions	$T_A = -40^\circ\text{C to }+85^\circ\text{C}$		±0.1	±0.15		±0.15	μV/°C
	Input Offset Voltage (all models) vs Time vs Power Supply $T_A = -40^\circ\text{C to }+85^\circ\text{C}$ Channel Separation (dual, quad)	PSRR $V_{I1} = \pm 2\text{V to } \pm 18\text{V}$ $V_{I2} = \pm 2\text{V to } \pm 18\text{V}$ dc		0.2	±0.3		±0.5	μV/V μV/V μV/V
Bias INPUT BIAS CURRENT Input Bias Current $T_A = -40^\circ\text{C to }+85^\circ\text{C}$ Input Bias Current $T_A = -40^\circ\text{C to }+85^\circ\text{C}$	I_B		±0.5	±1		±2	±2.8	nA
	I_{CS}		±0.5	±1		±2	±4	nA
Noise NOISE Input Voltage Noise, $f = 0.1$ to 10Hz Input Voltage Noise, $f = 10\text{Hz}$ $f = 100\text{Hz}$ $f = 1\text{kHz}$ Current Noise Density, $f = 1\text{kHz}$	e_{nV}		0.22					μV/√Hz
	e_{nV}		0.026					μV/√Hz
	e_{nV}		12					nV/√Hz
	e_{nV}		8					nV/√Hz
i_{nA}		8					nA/√Hz	
i_{nA}		8					nA/√Hz	
i_{nA}		0.2					pA/√Hz	
V_{in} INPUT VOLTAGE RANGE Common-Mode Voltage Range Common-Mode Rejection $T_A = -40^\circ\text{C to }+85^\circ\text{C}$	V_{CM}		(V ₋)+2		(V ₋)-2			V
	CMRR	$V_{CM} = (V_+) + 2\text{V to } (V_+) - 2\text{V}$ $V_{CM} = (V_-) + 2\text{V to } (V_-) - 2\text{V}$	130	140	115	115		dB
			128		115			dB
Z_{in} INPUT IMPEDANCE Common-Mode $V_{CM} = (V_+) + 2\text{V to } (V_+) - 2\text{V}$	Z_{in}		100 3					MΩ μF
			250 3					Ω μF
Gain OPEN-LOOP GAIN Open-Loop Gain $V_{I1} = \pm 15\text{V}$, $G = 1$, 10V Step $T_A = -40^\circ\text{C to }+85^\circ\text{C}$	A_{OL}		$V_{I1} = (V_+) + 0.65\text{V to } (V_+) - 1.2\text{V}$, $R_L = 10\text{k}\Omega$ $V_{I1} = (V_-) + 0.65\text{V to } (V_-) - 1.5\text{V}$, $R_L = 20\text{k}\Omega$ $V_{I1} = (V_-) + 0.65\text{V to } (V_-) - 1.5\text{V}$, $R_L = 20\text{k}\Omega$	140	154			dB
			126	134				dB
			126					dB
BW FREQUENCY RESPONSE Gain Slew Rate Settling Time, 0.1% 0.01% Overload Recovery Time Total Harmonic Distortion + Noise (THD+N) 1kHz, $G = 1$, $V_{O1} = 3.5\text{Vrms}$	GBW		1					MHz
	SR		0.8					V/μs
		$V_{O1} = \pm 15\text{V}$, $G = 1$, 10V Step		14				μs
		$V_{O1} = \pm 15\text{V}$, $G = 1$, 10V Step		16				μs
		$V_{O1} = \pm 15\text{V}$, $G = 1$, 10V Step		3				μs
I_{short} OUTPUT Voltage Output $T_A = -40^\circ\text{C to }+85^\circ\text{C}$ Short-Circuit Current $R_L = 10\text{k}\Omega$ $R_L = 2\text{k}\Omega$ $R_L = 20\Omega$ Short-Circuit Current I_{CS} Capacitive Load Drive C_{load}	V_{O1}	$R_L = 10\text{k}\Omega$ $R_L = 2\text{k}\Omega$ $R_L = 20\Omega$	(V ₋)+1.5 (V ₋)-1.5 (V ₋)+1.5	(V ₋)+1.2 (V ₋)-1.2 (V ₋)+1.5				V
			(V ₋)+1.5 (V ₋)-1.5	(V ₋)+1.5 (V ₋)-1.5				V
			(V ₋)+1.5 (V ₋)-1.5	(V ₋)+1.5 (V ₋)-1.5				V
			(V ₋)+1.5 (V ₋)-1.5	(V ₋)+1.5 (V ₋)-1.5				V
			±35					mA
			See Typical Curve					

Datasheet



*R. Tummala, Fundamentals of Microsystems Packaging, 2001.

Standard Specification Tests

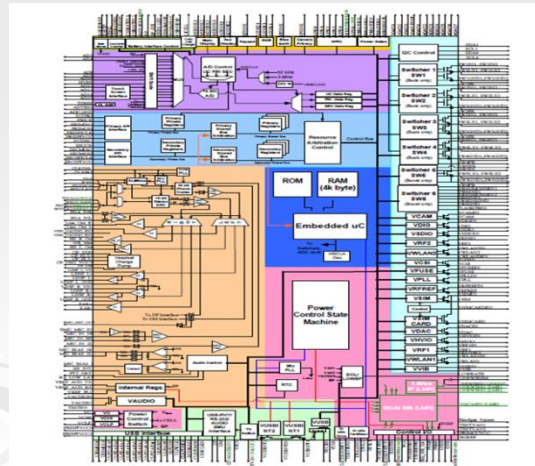
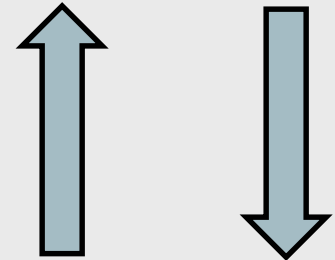


Key Issues:

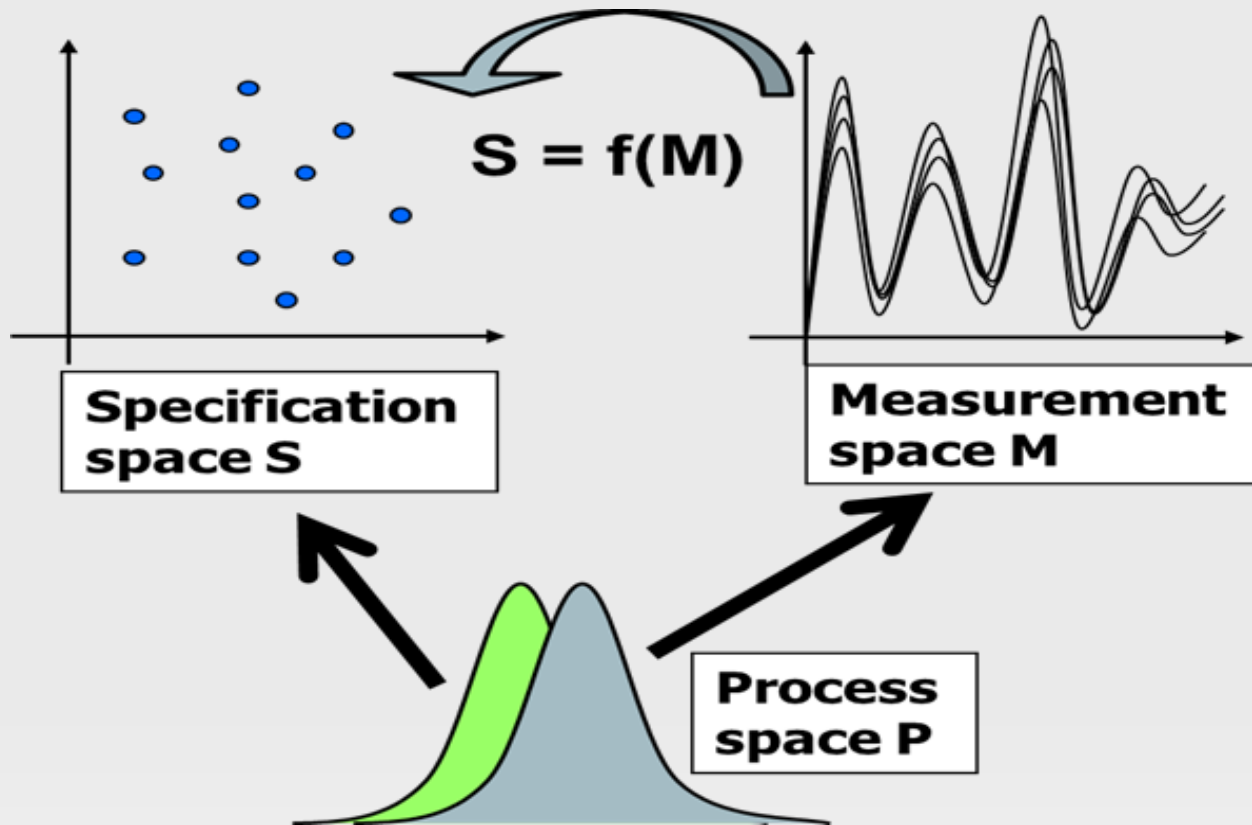
Manufacturing test time: Relay settling time (ms) \gg actual test time (usec) ! Test multiple specs.

Built-in test of complex specifications: Difficult to place test instruments and circuitry on-chip for multiple specifications !

Post-manufacture and field performance tuning: Tune *multiple* specs while minimizing power ? Need to tune devices *without extended test costs*.

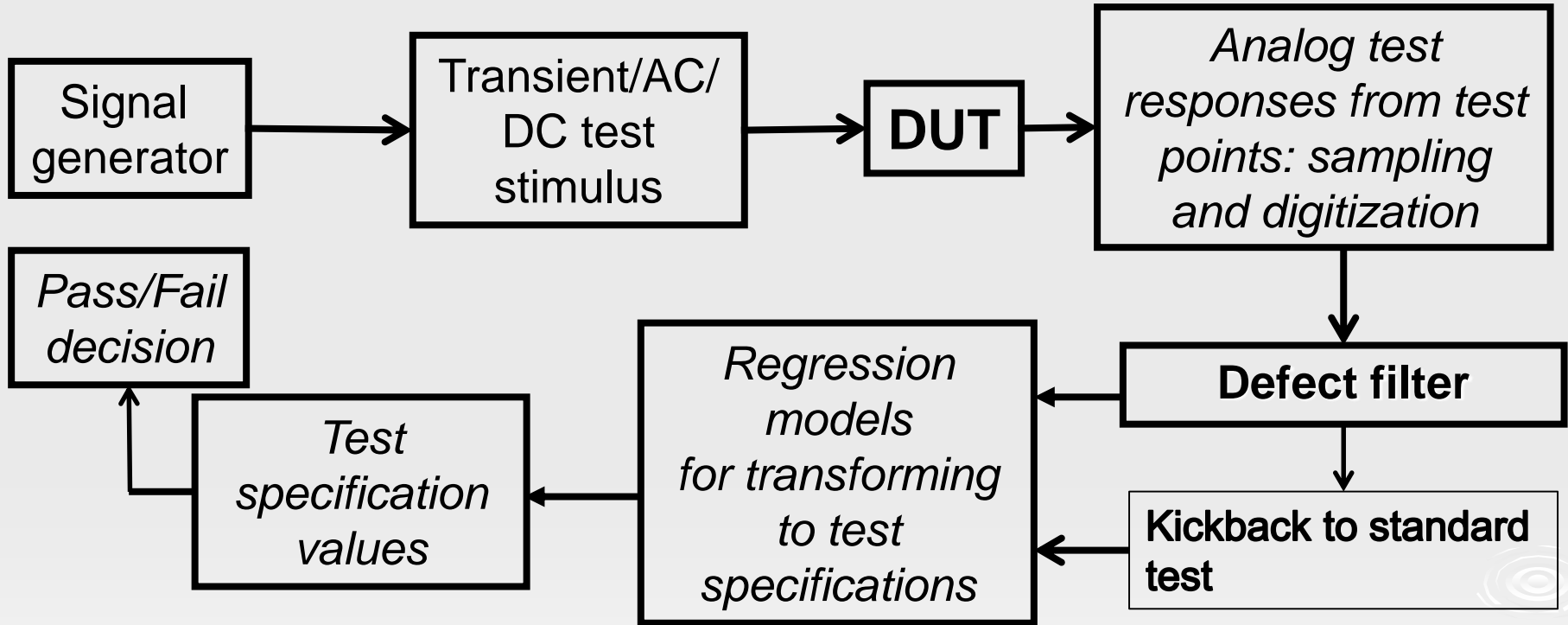


Alternate Tests: Key Principles



- The mapping $S=f(M)$ is derived using nonlinear regression (multiple adaptive regression splines: MARS)

Signature Test Methodology



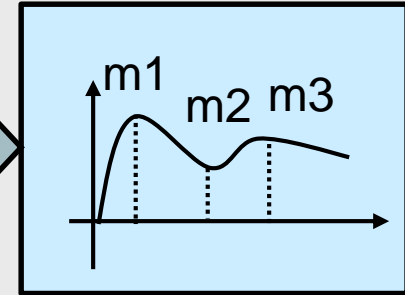
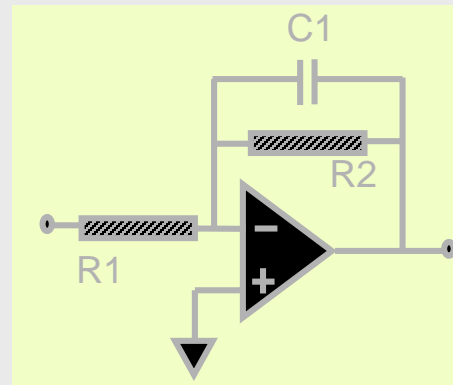
Test Stimulus Generation

Test Stimulus



Optimize $x(t)$

Circuit-under-test



Measurements

DC Gain
Bandwidth
.....

Specifications

S2

S1

$$d_s = |S - S^*|$$

Test Generation: *Maximize statistical correlation between measurements and specifications*

Stimulus Search

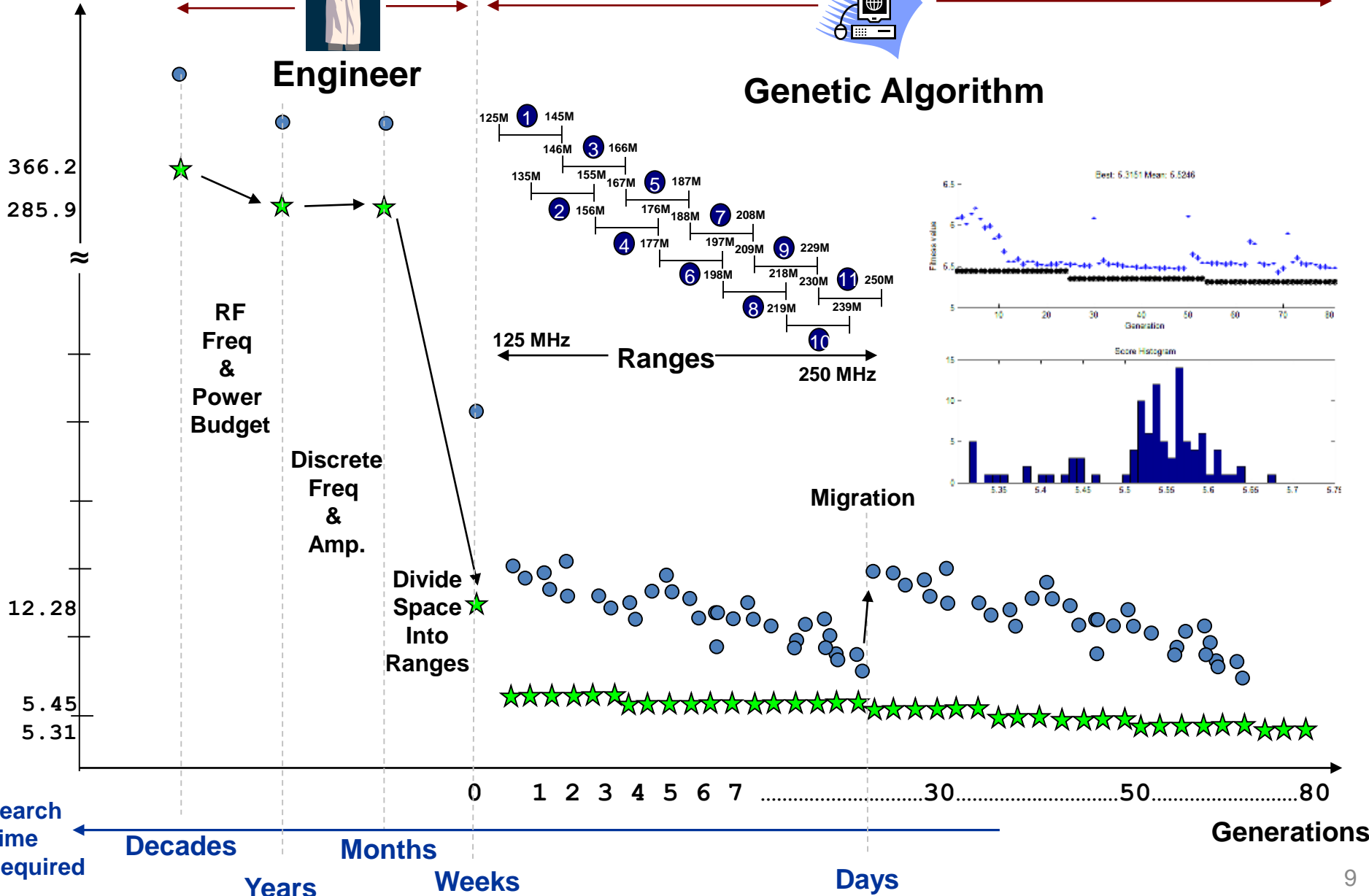
- ★ Best fitness value in a generation
- Mean fitness value in a generation



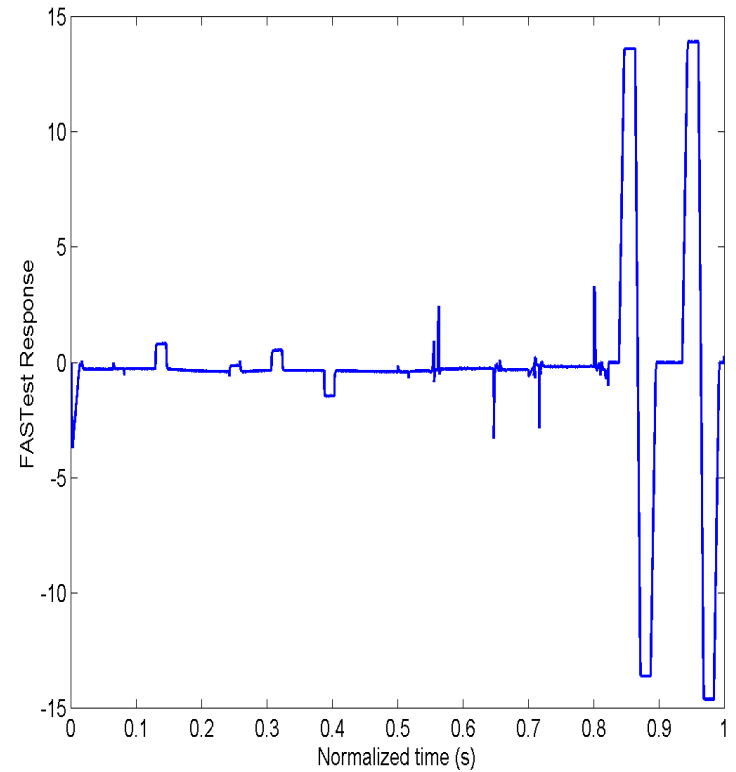
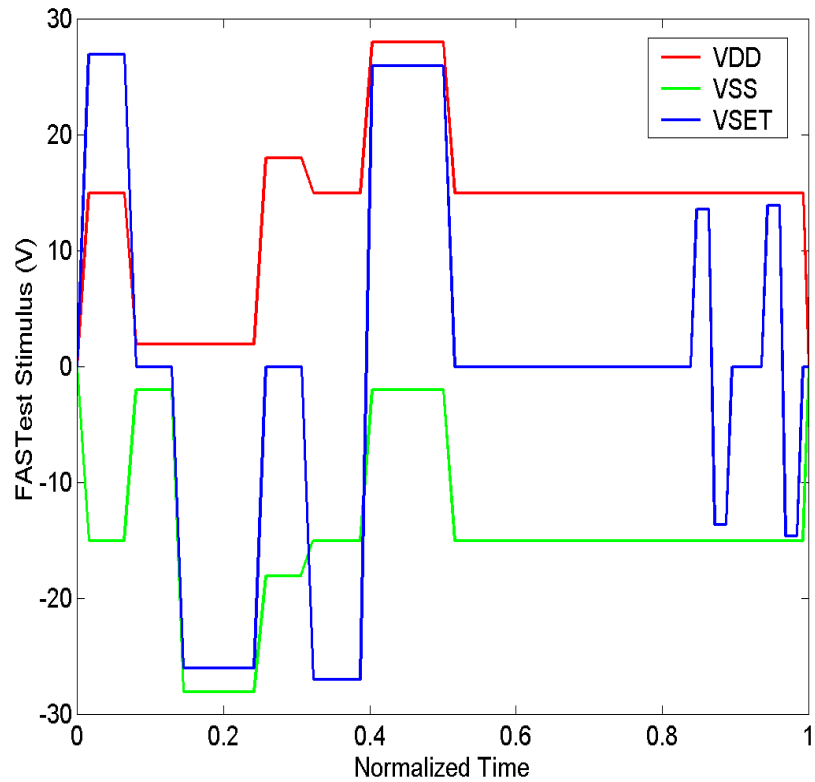
Engineer



Genetic Algorithm

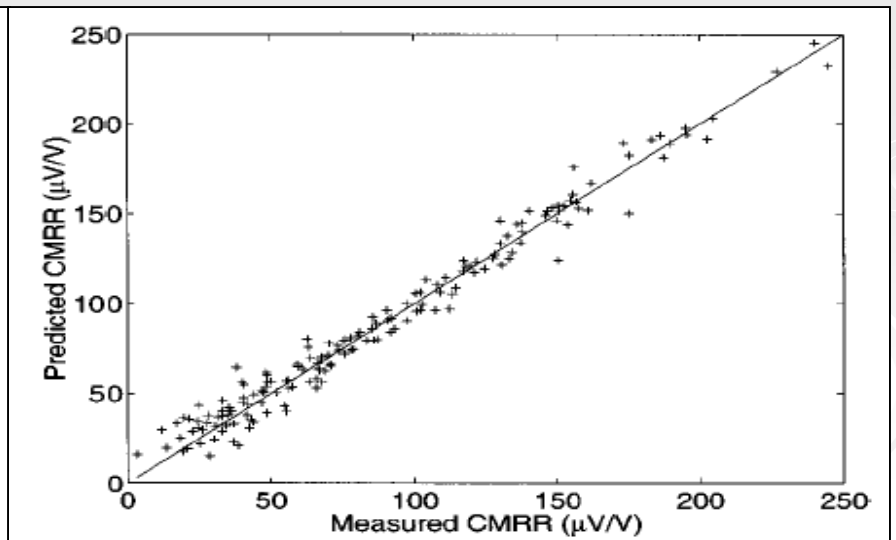
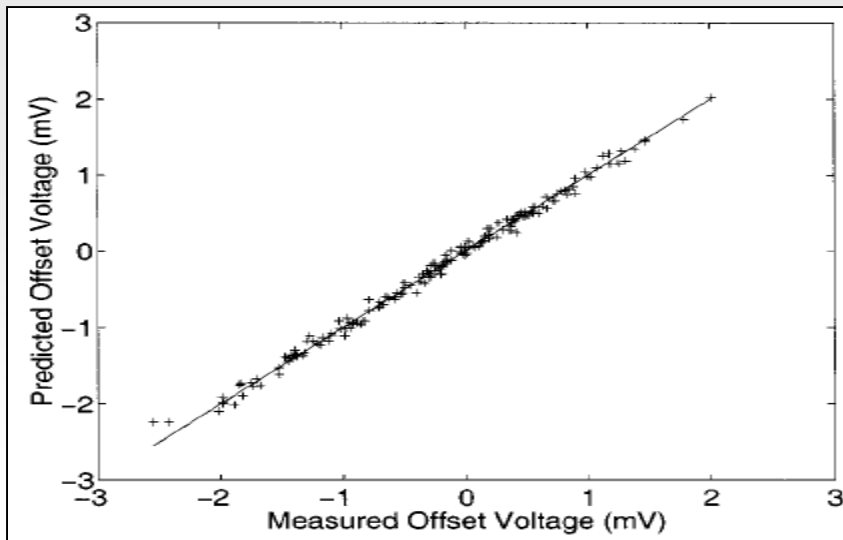
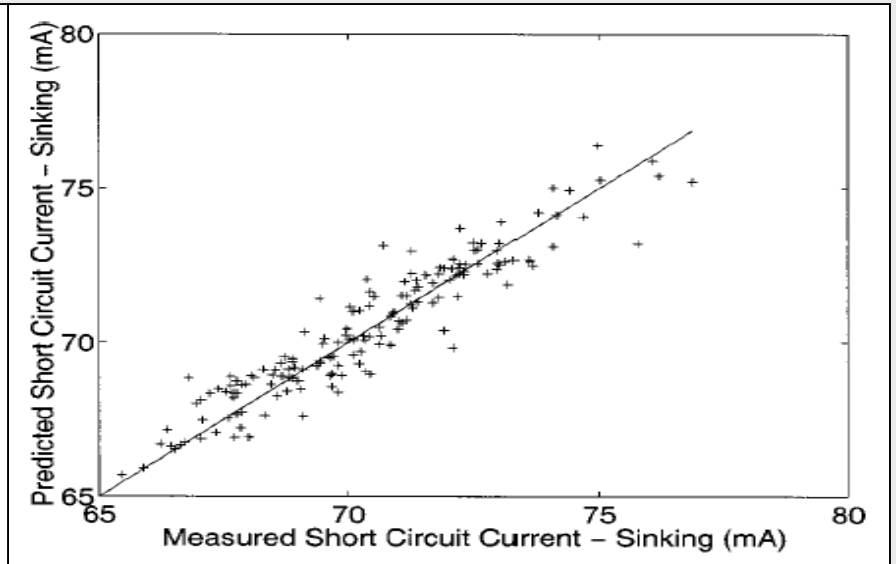
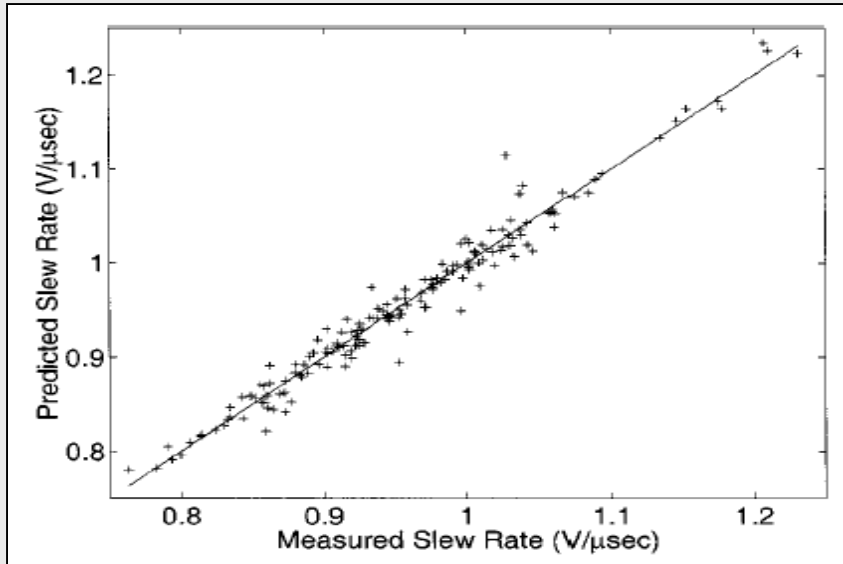


TI Precision Opamp



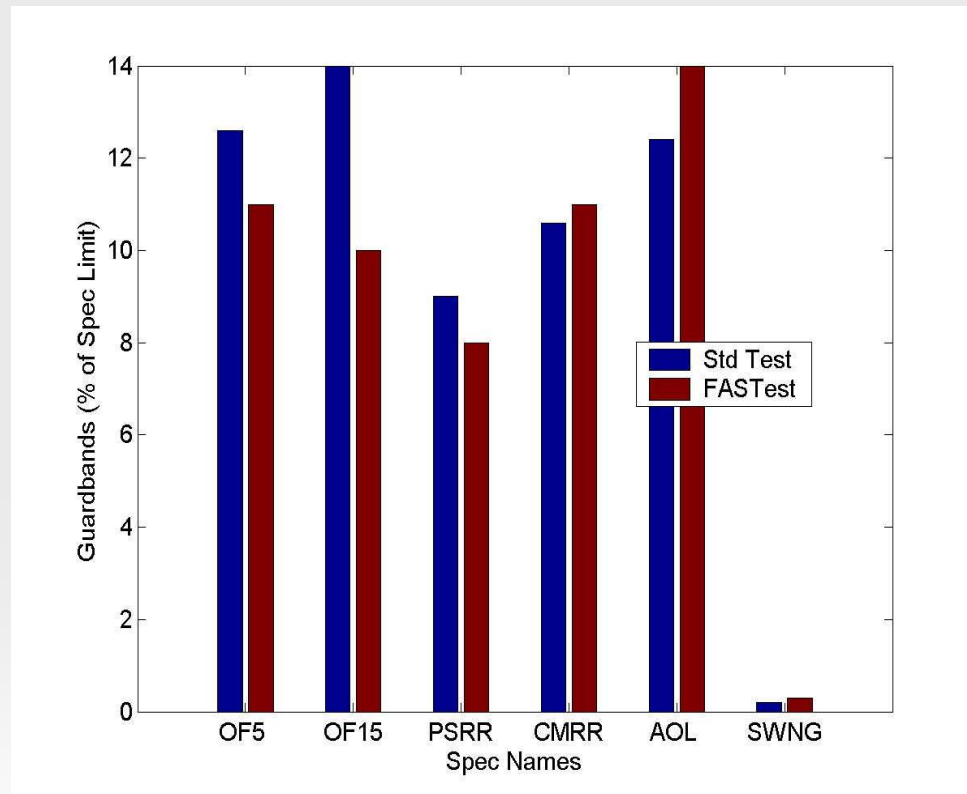
>3X test time reduction

Alternate Test: Performance

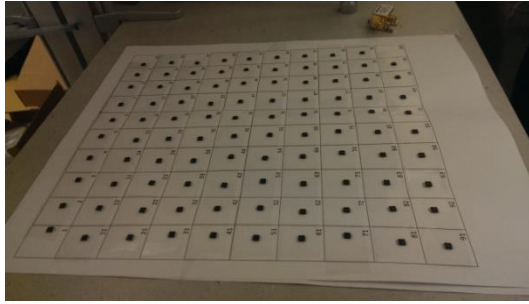


Capability Study (Guardbands)

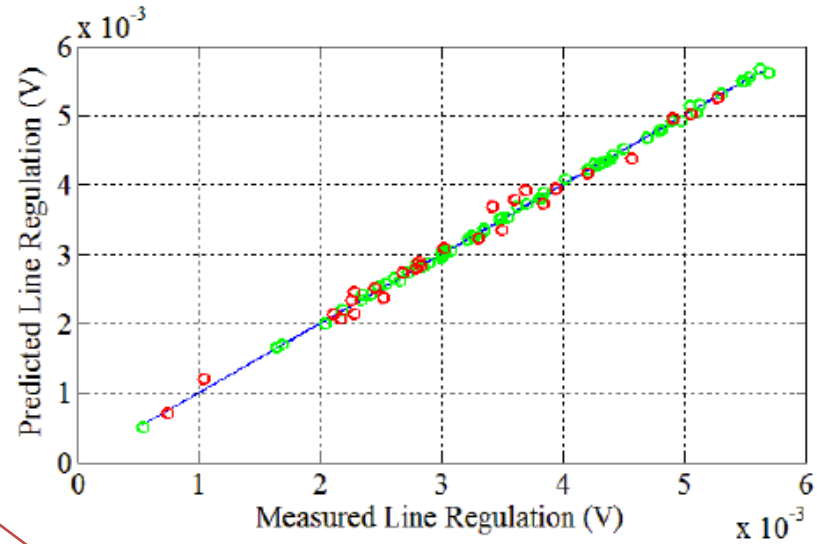
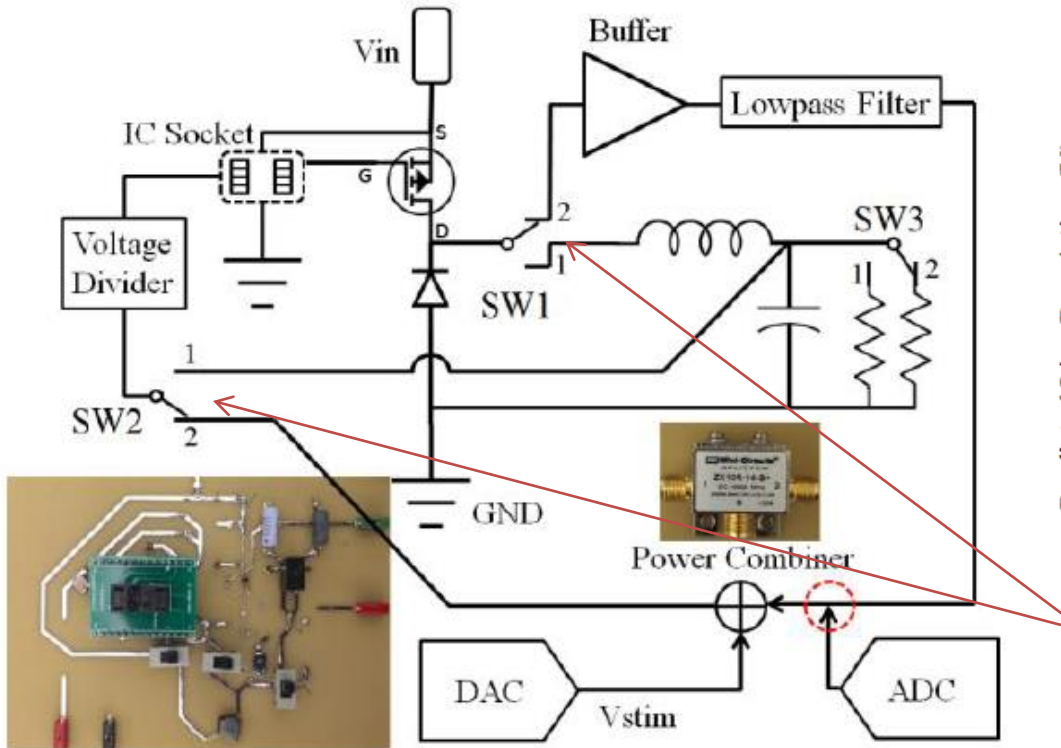
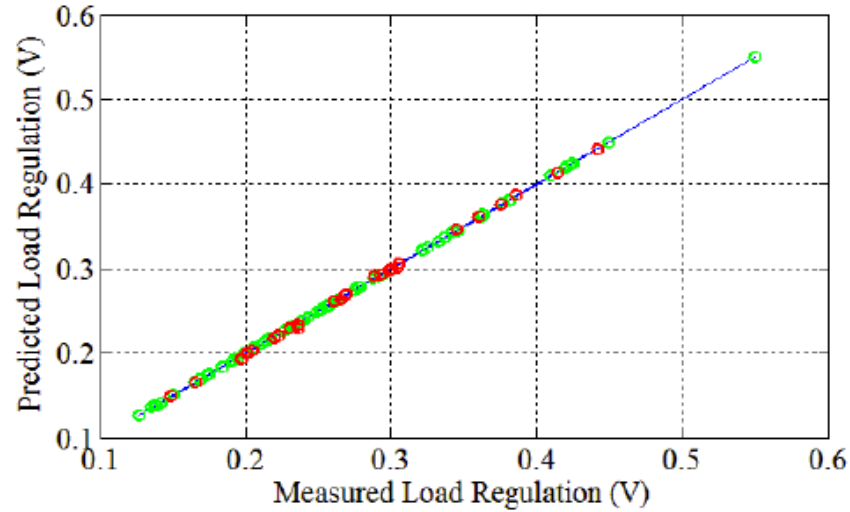
- For most specs, identical or better guardbands resulted



Hysteretic Buck Converter

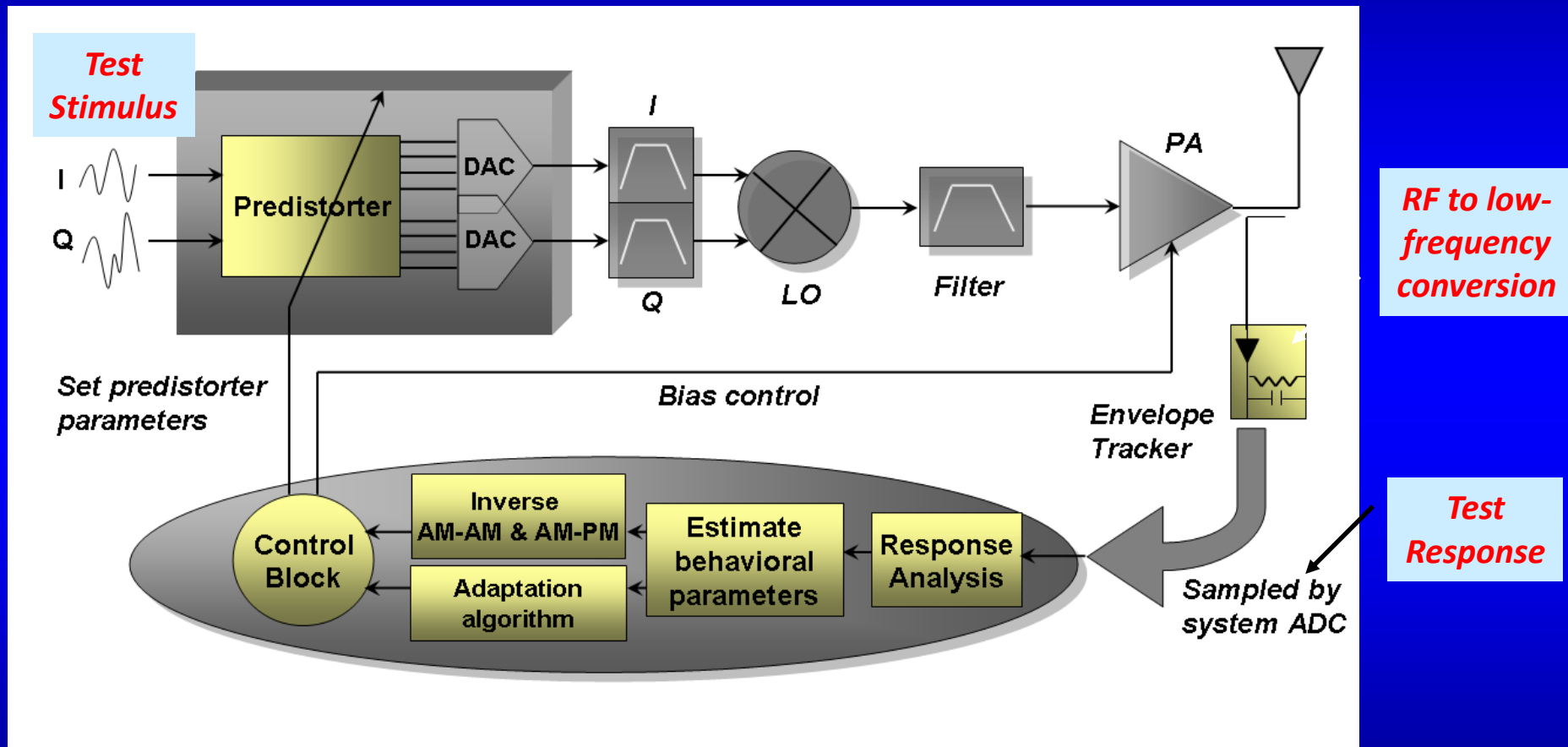


100 chips (LM3485)



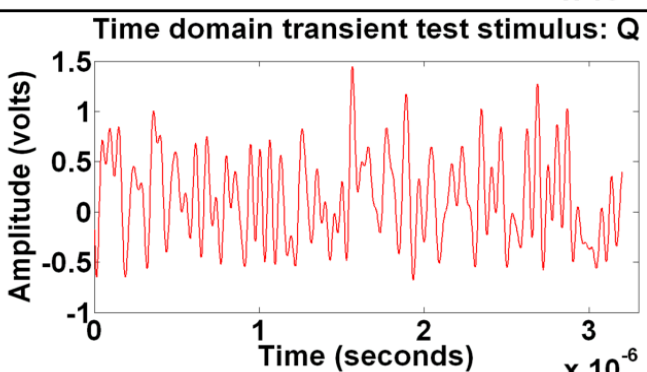
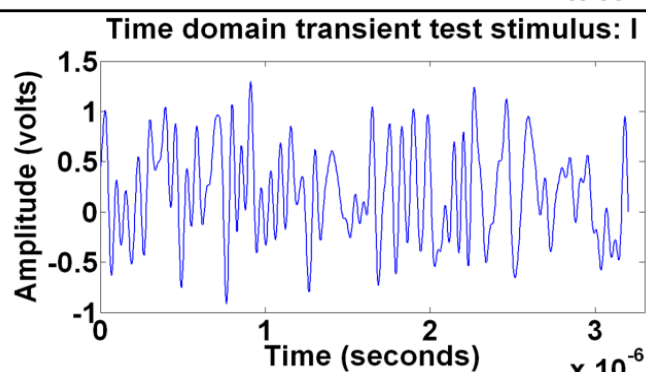
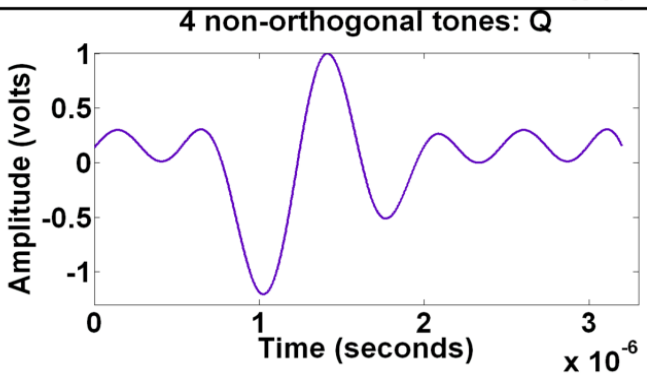
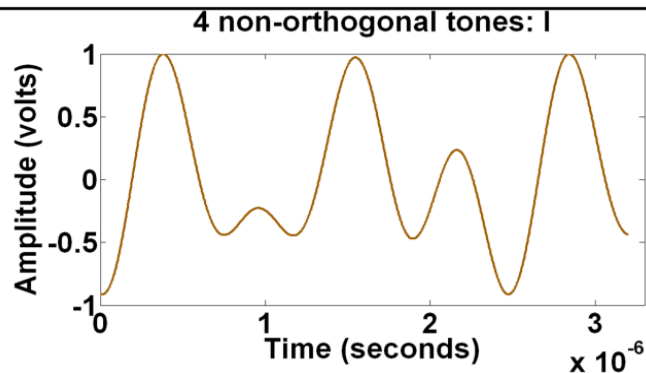
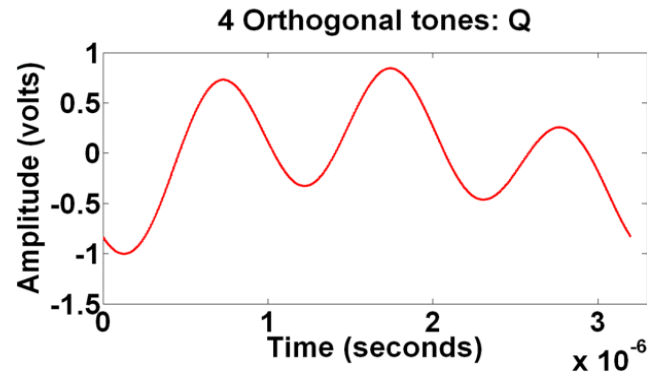
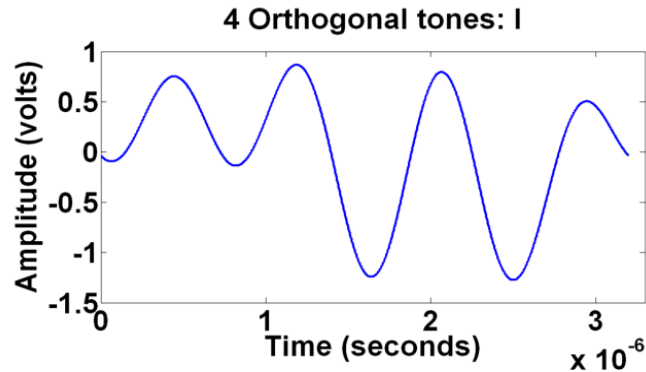
SW1 and SW2 in positions 2 for proposed test and position 1 for conventional test

Signature-BIST: Overview



Ref: Variyam, Chatterjee, TCAD 2000

Optimized Diagnostic Tests



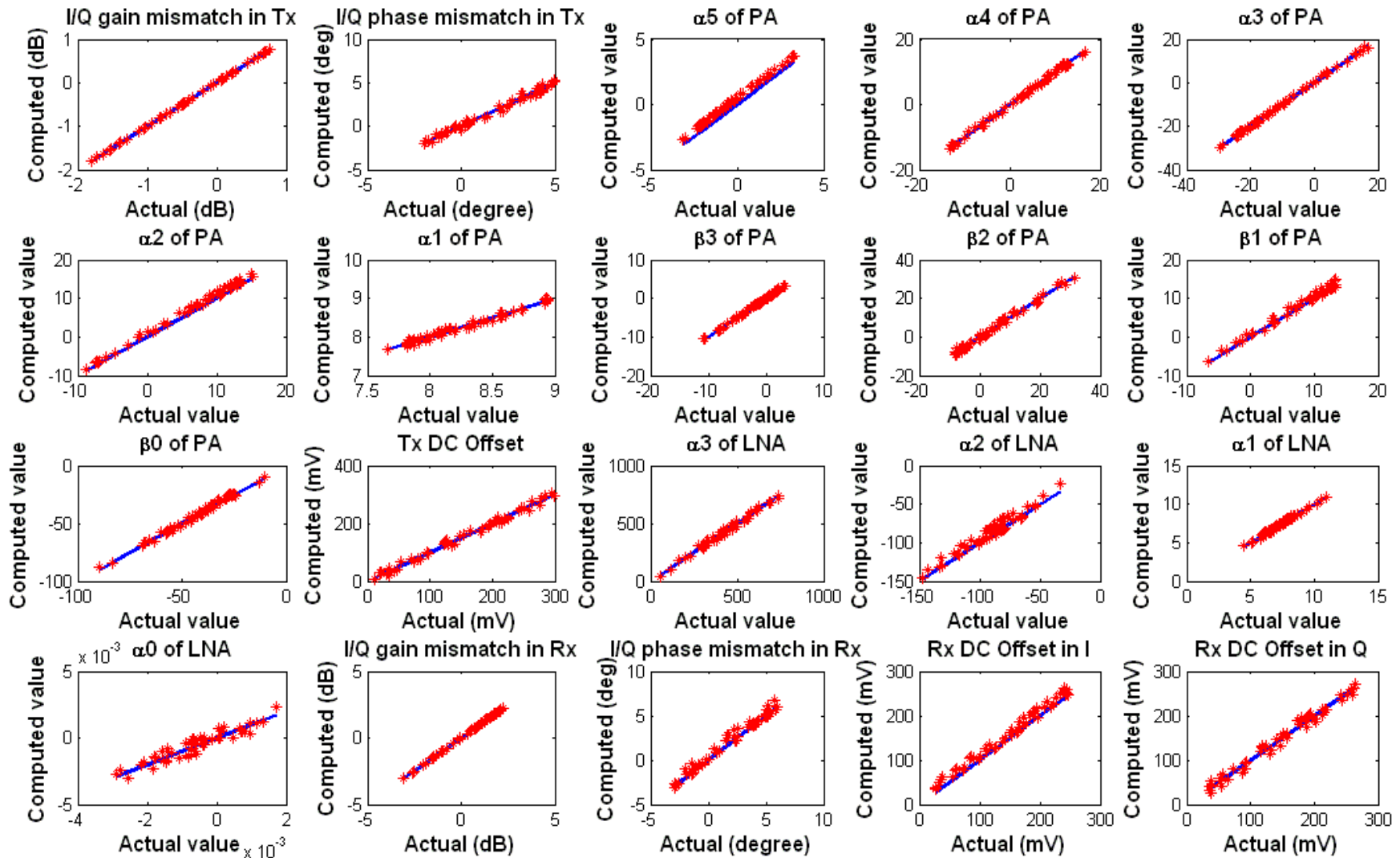
Orthogonal tones

Non-orthogonal tones

Time domain test stimulus

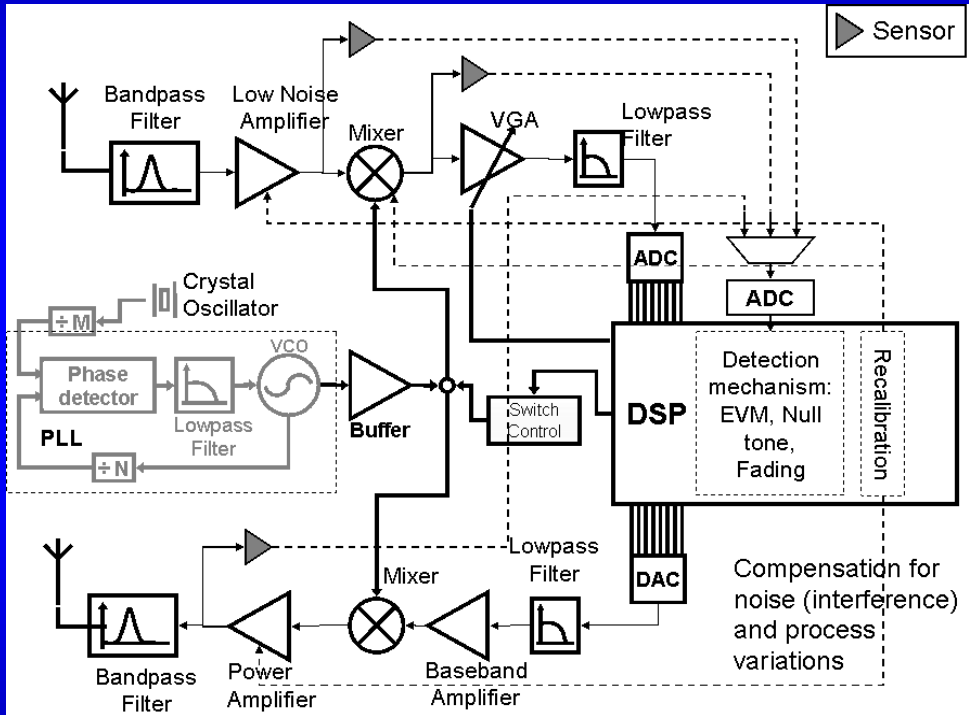
Signature Based Model Parameter Estimation

Ability to diagnose parameters of embedded modules !

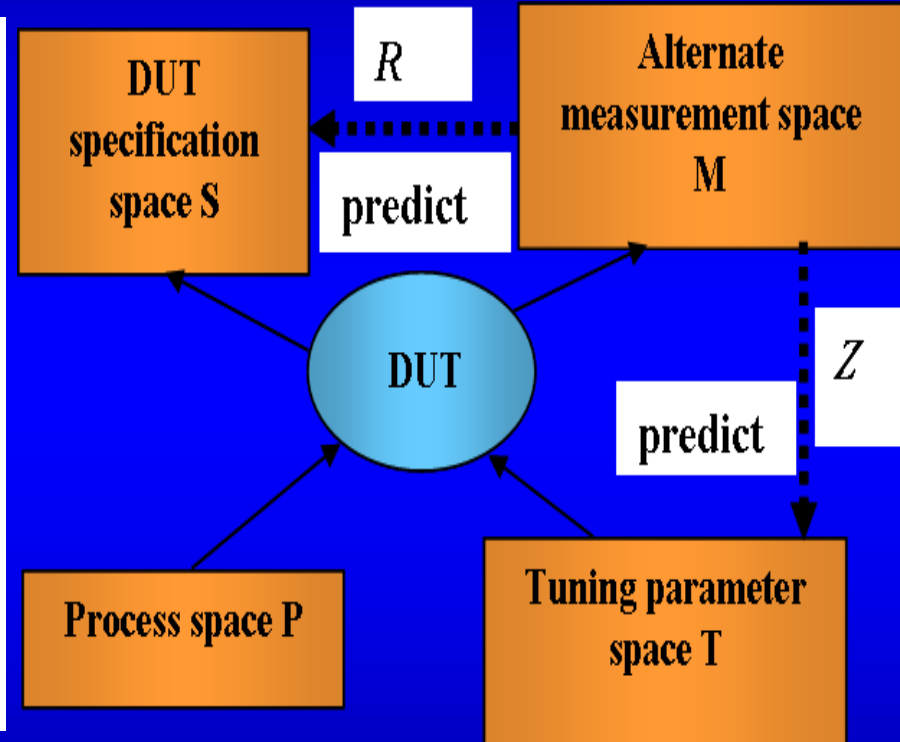


Tuning: Learning Driven

Tuning Architecture

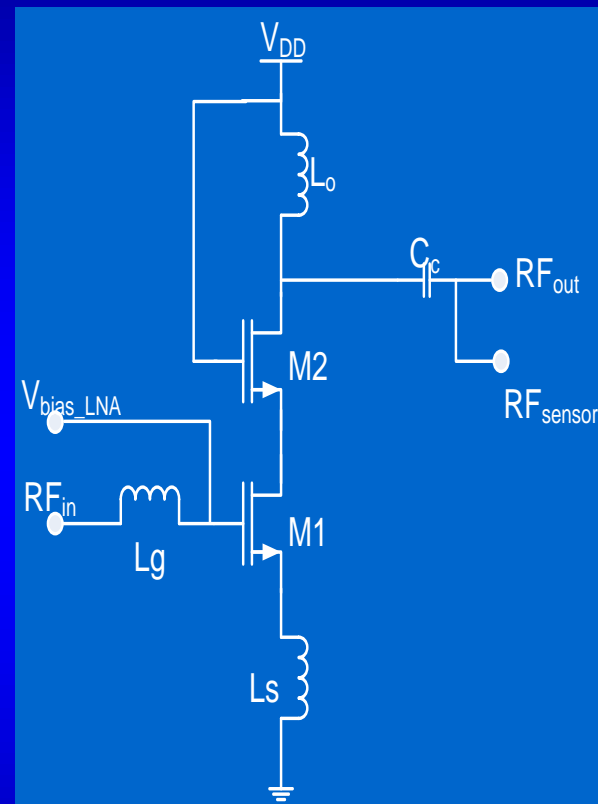
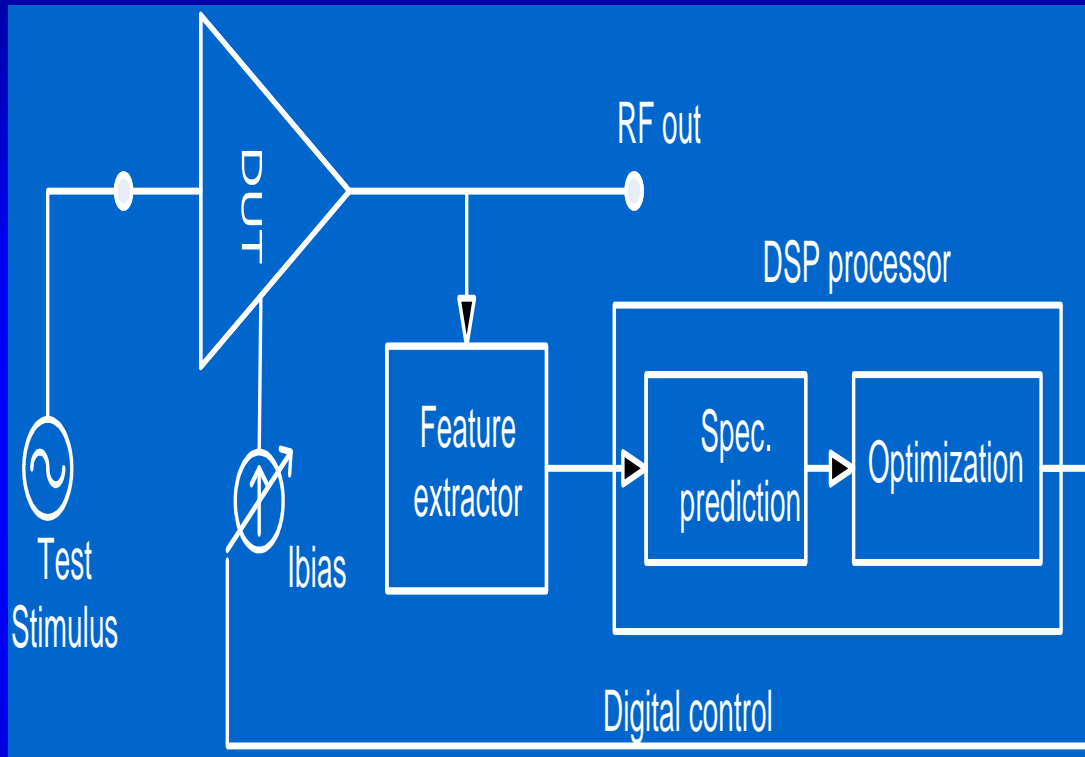


Supervised Learning

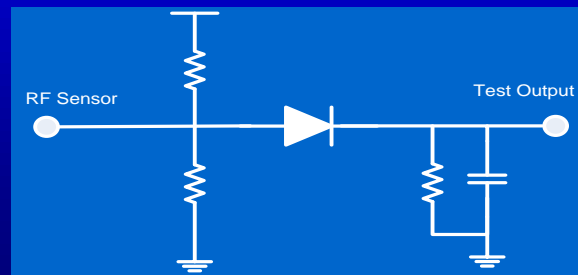


- Ability to tune for multiple specs using single data acquisition
- Ability to perform near optimal tuning
- Minimal on-chip hardware overhead

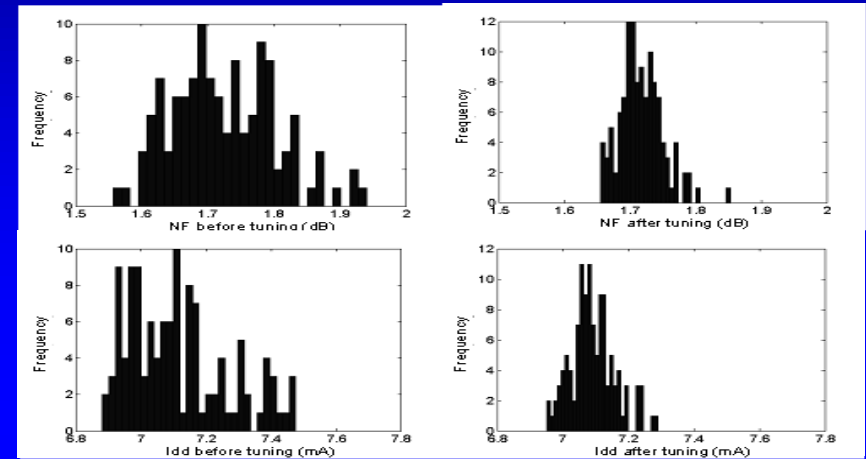
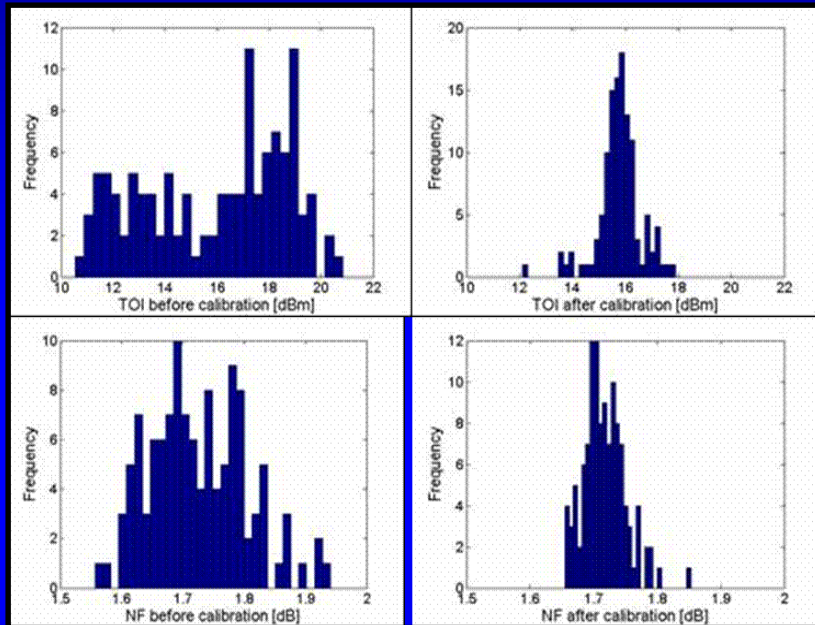
Learning driven tuning algorithms



Need accurate learning algorithms!

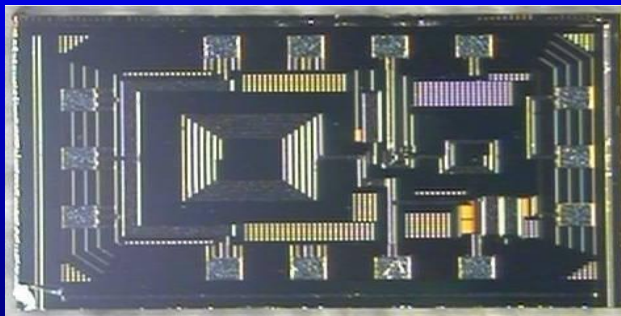


Learning driven tuning algorithms



NF (top) and Idd (bottom) before tuning.

NF (top) and Idd (bottom) after tuning



Self-healing LNA !

70% to 99% yield improvement

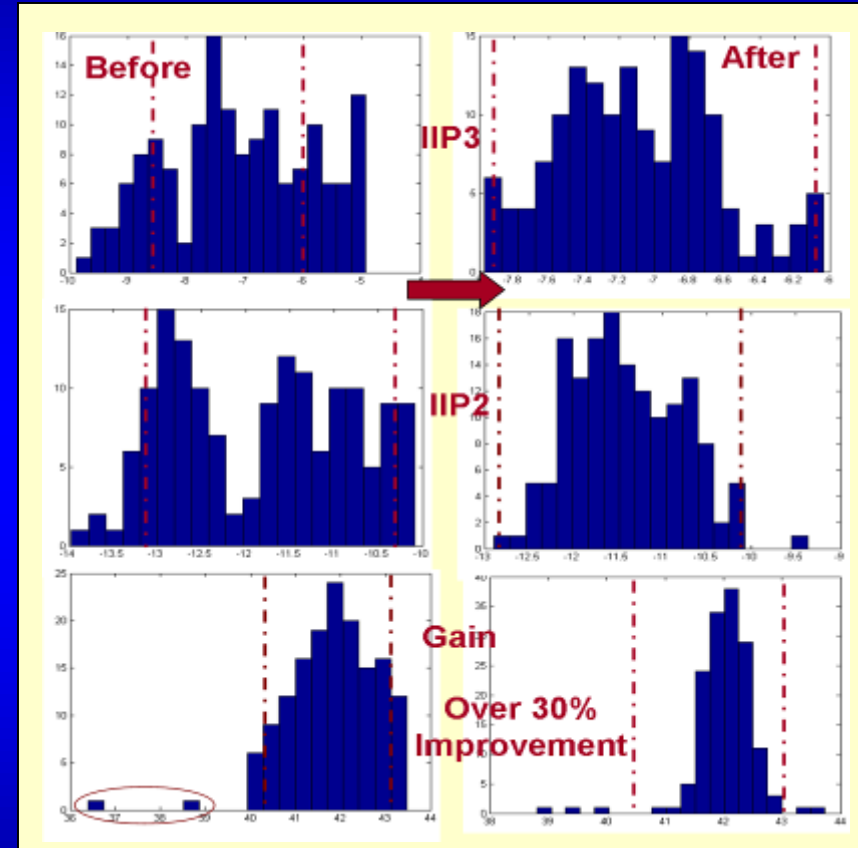
Experimental Results: Full Receiver

Nominal Specs

	Gain	IIP2	IIP3
Nominal	42.5 dB	-11.5 dBm	- 7dBm
Lower bound	41.5 dB	-12.5 dBm	- 8dBm
Upper bound	43.5 dB	-10.5 dBm	-6 dBm

One-Instance (P1)

	Gain	IIP2	IIP3
Before	40.1	-10	-5.3
After	41.5726	-11	-7.2569

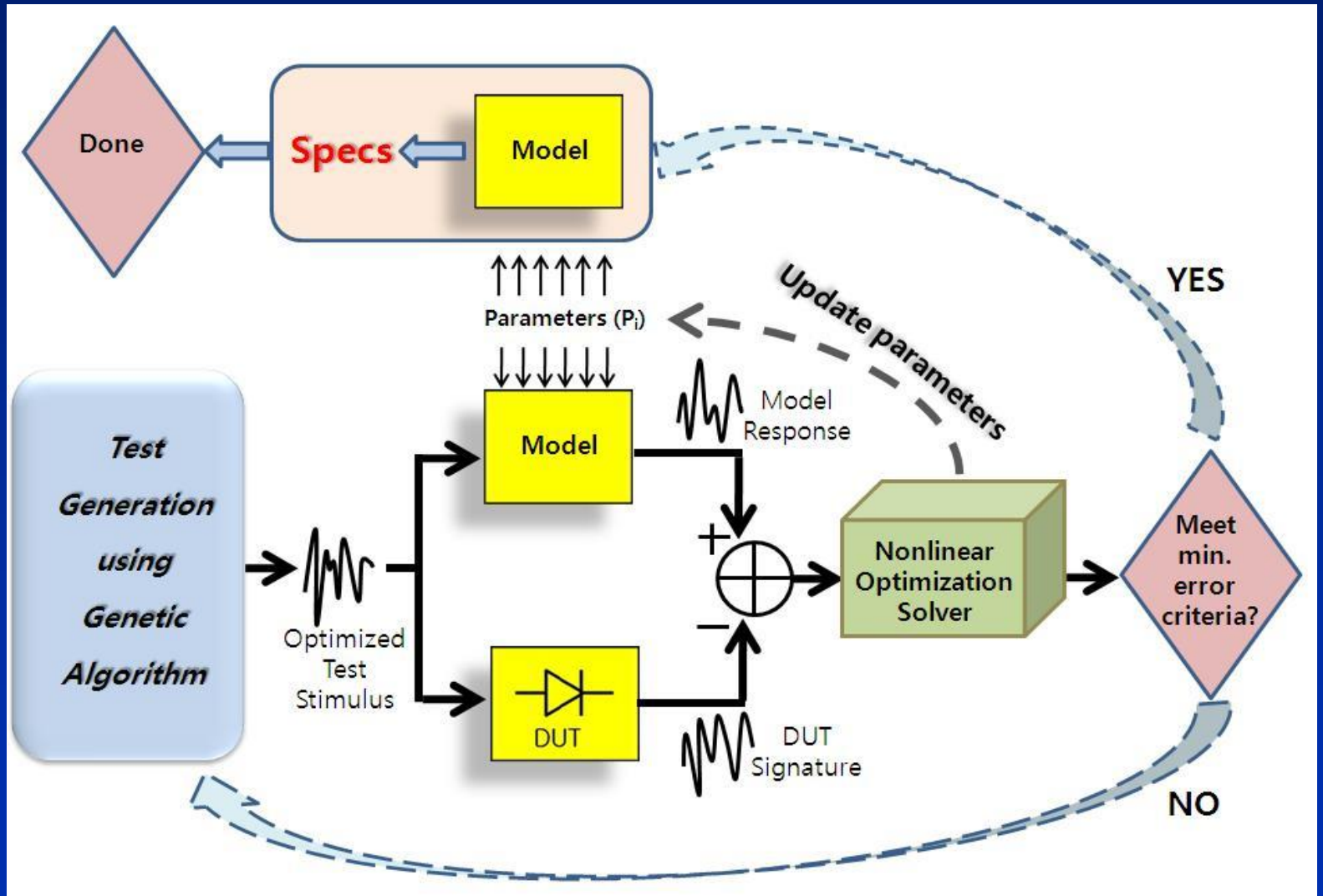


- 207 possible knob combinations (P1) for yield recovery
- Power conscious knob combination (P1) : 0.5724W
- Converged Knob combination (P1) : 0.5724W

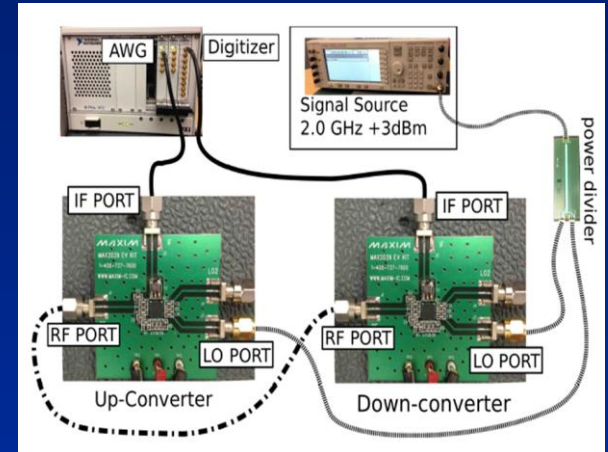
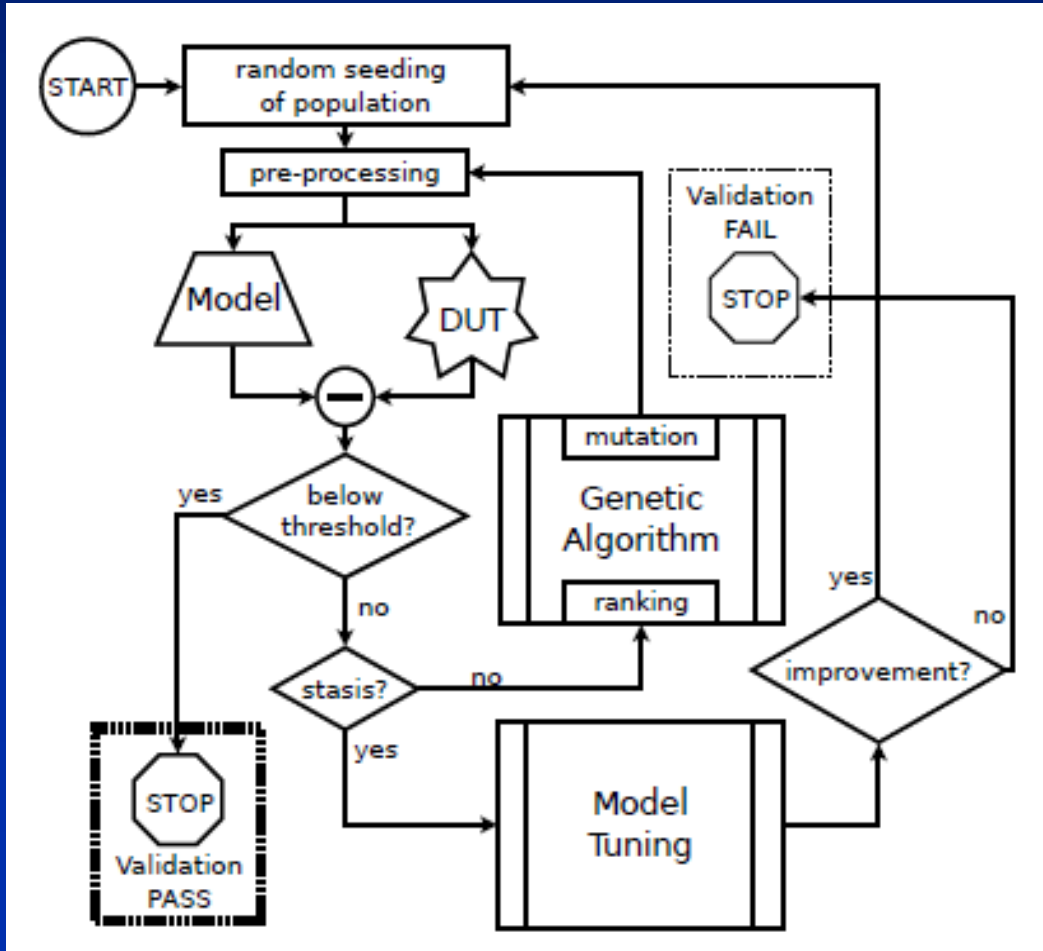
Post-Silicon Challenges

- Models for design bugs are not known a-priori and must be detected, learned and diagnosis
- Need to automate generation of bug models using learning algorithms
- Diagnosed bugs must eventually be mapped to physical design parameters

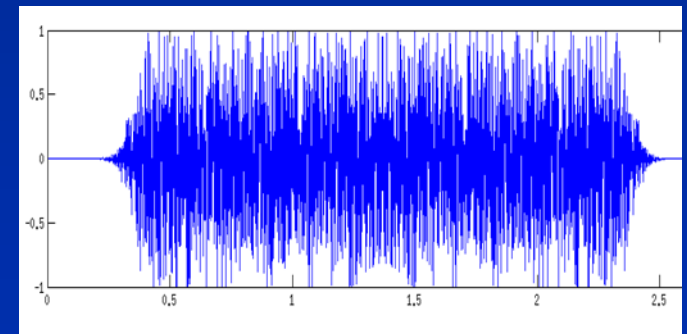
Model Tuning



Test Stimulus Generation for Exposing Design Bugs

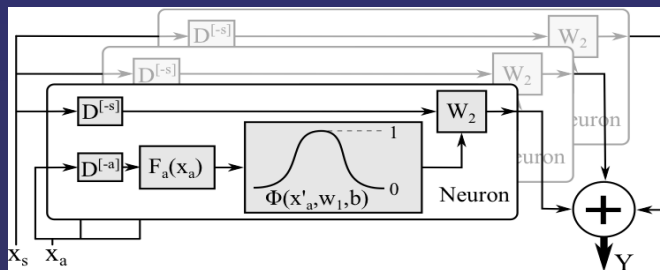
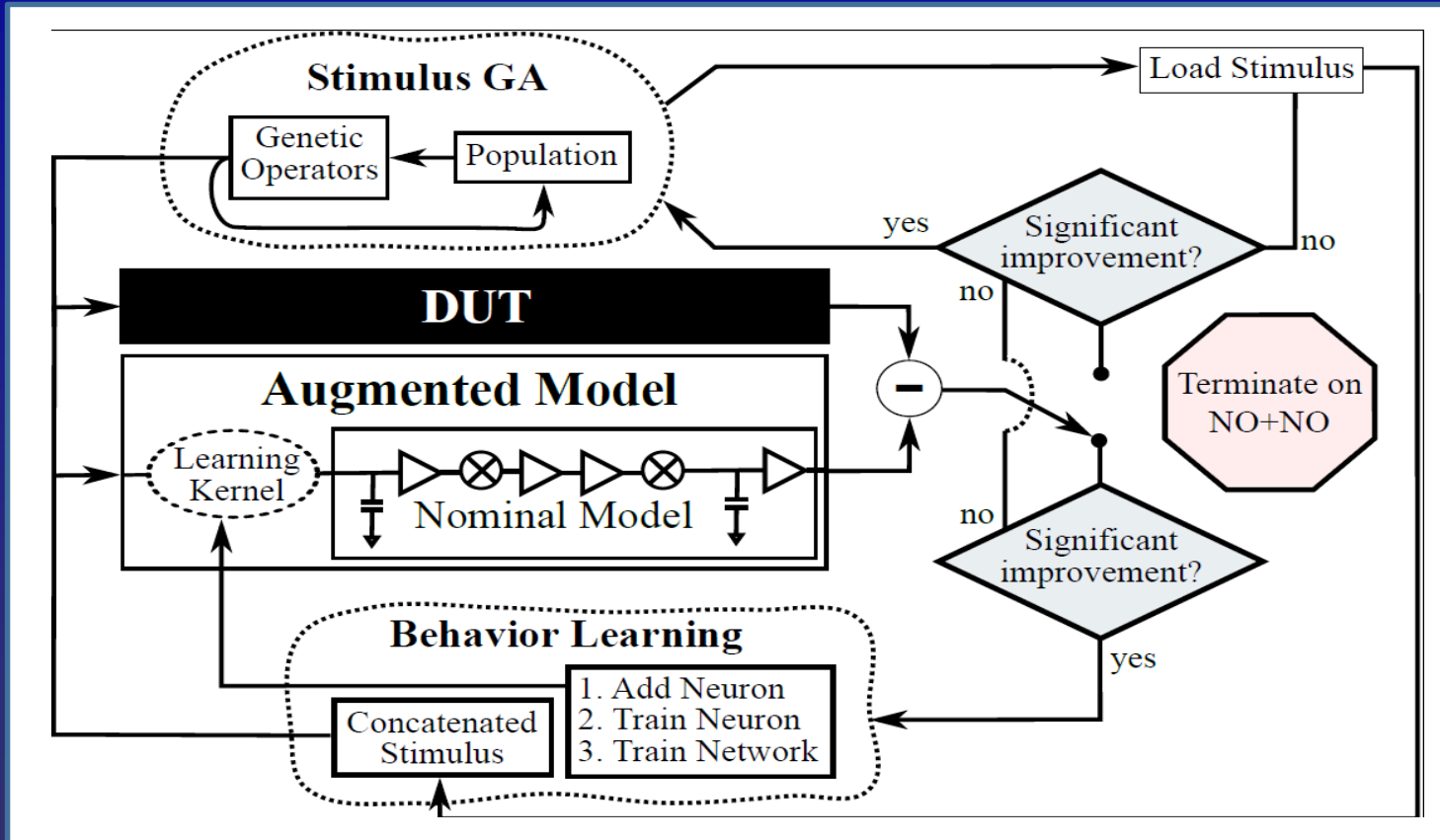


Test setup



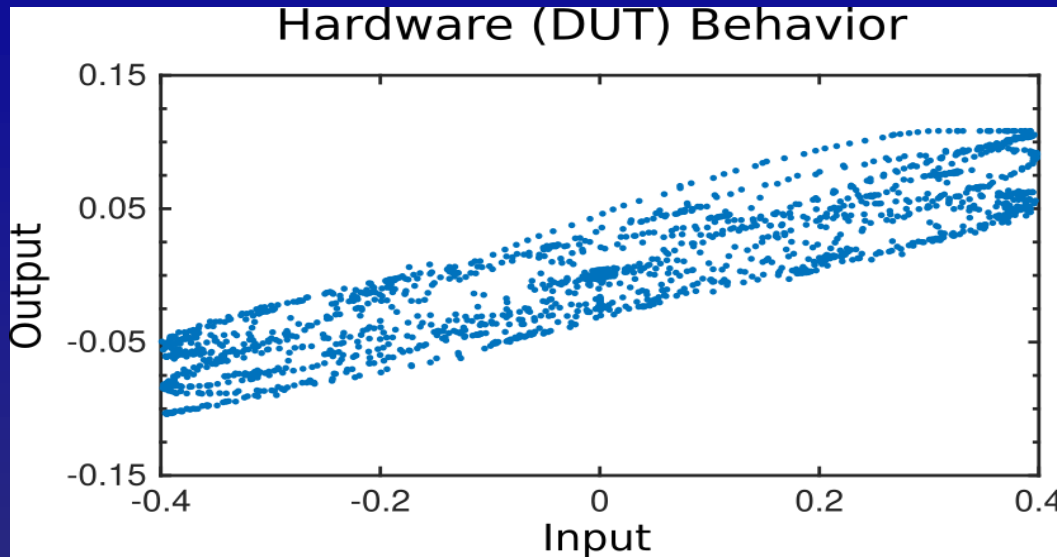
Best stimulus

System Level Bug Learning

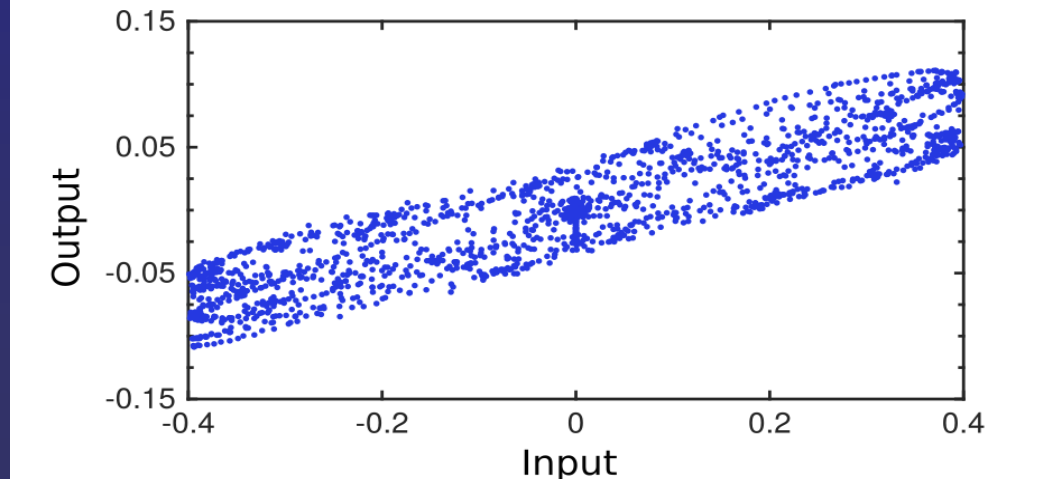


Sparse Weiner learning kernel

Experimental Results: Maxim MAX2242 RF PA

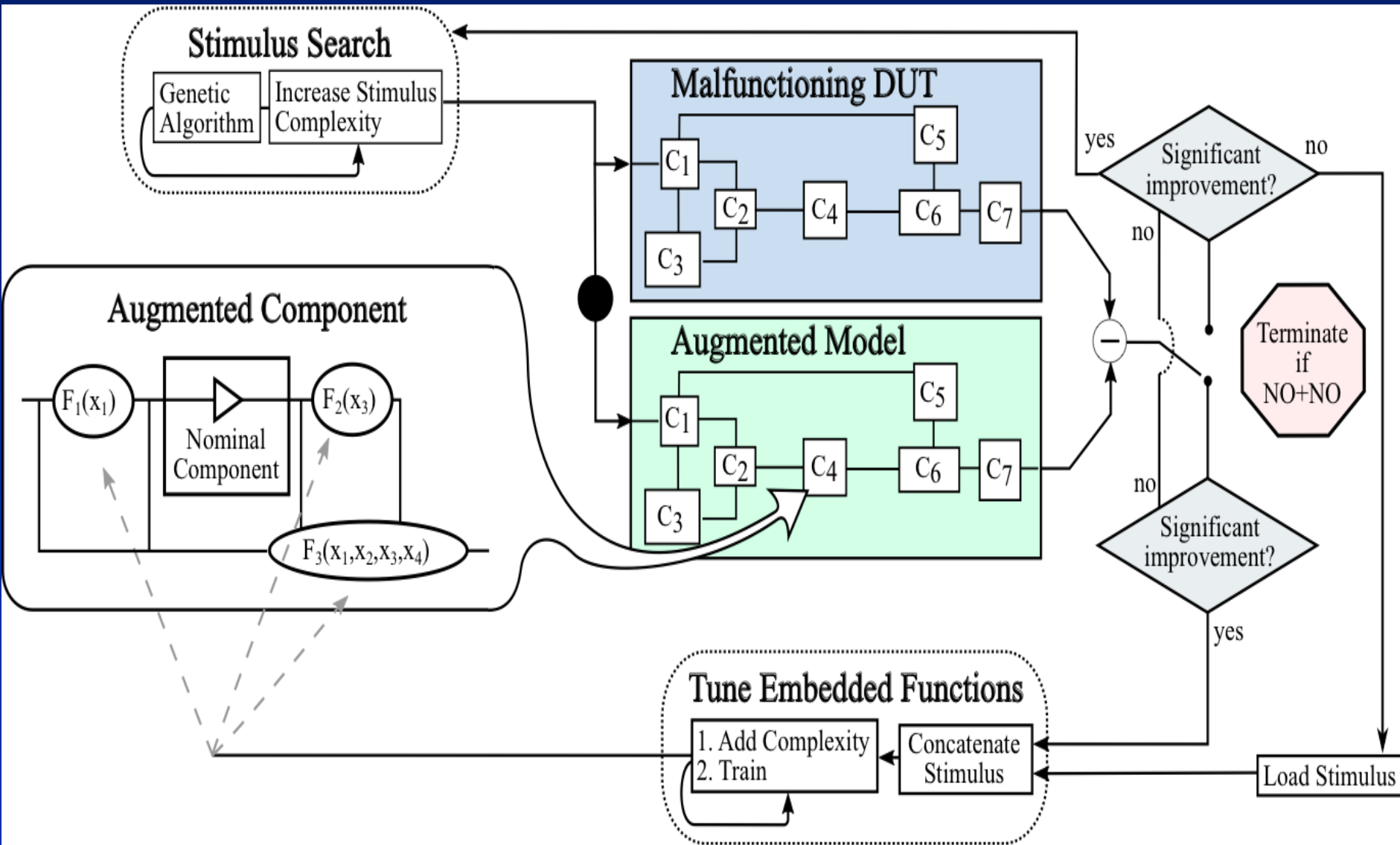


Model Behavior After Augmentation and Training

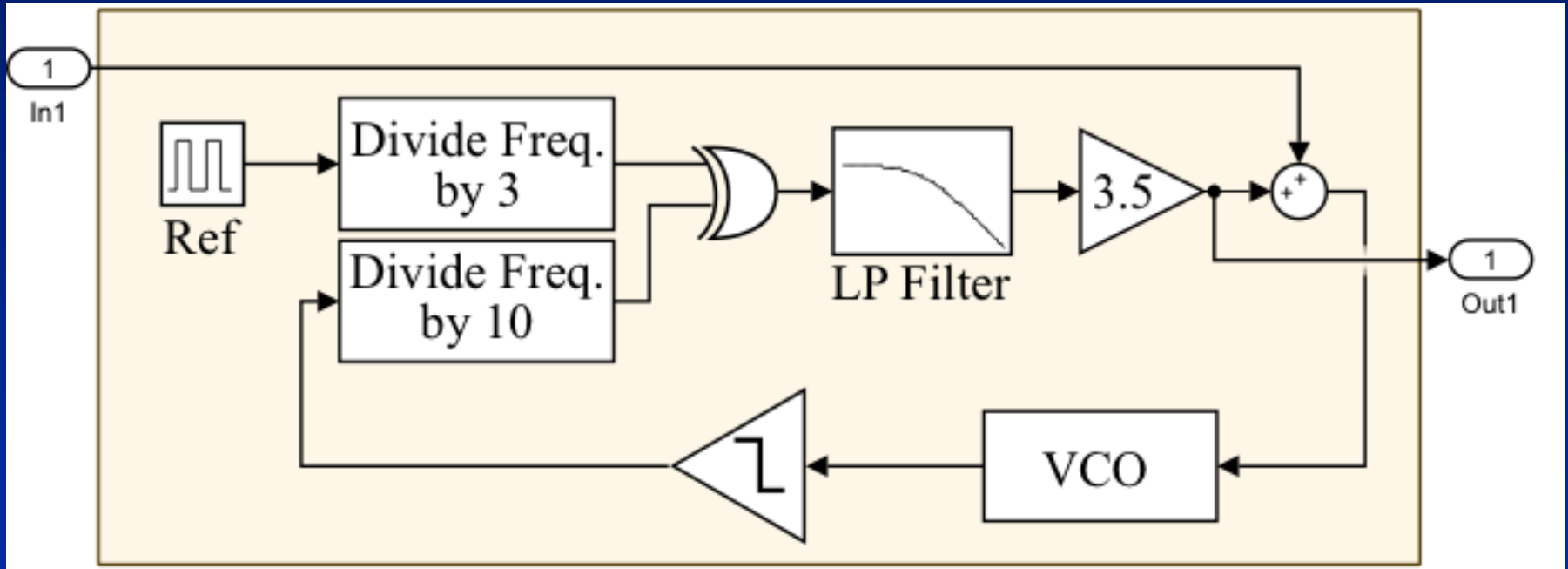


**Captures
hysteresis
and memory
effects
automatically**

Diagnosis of Static Design Bugs

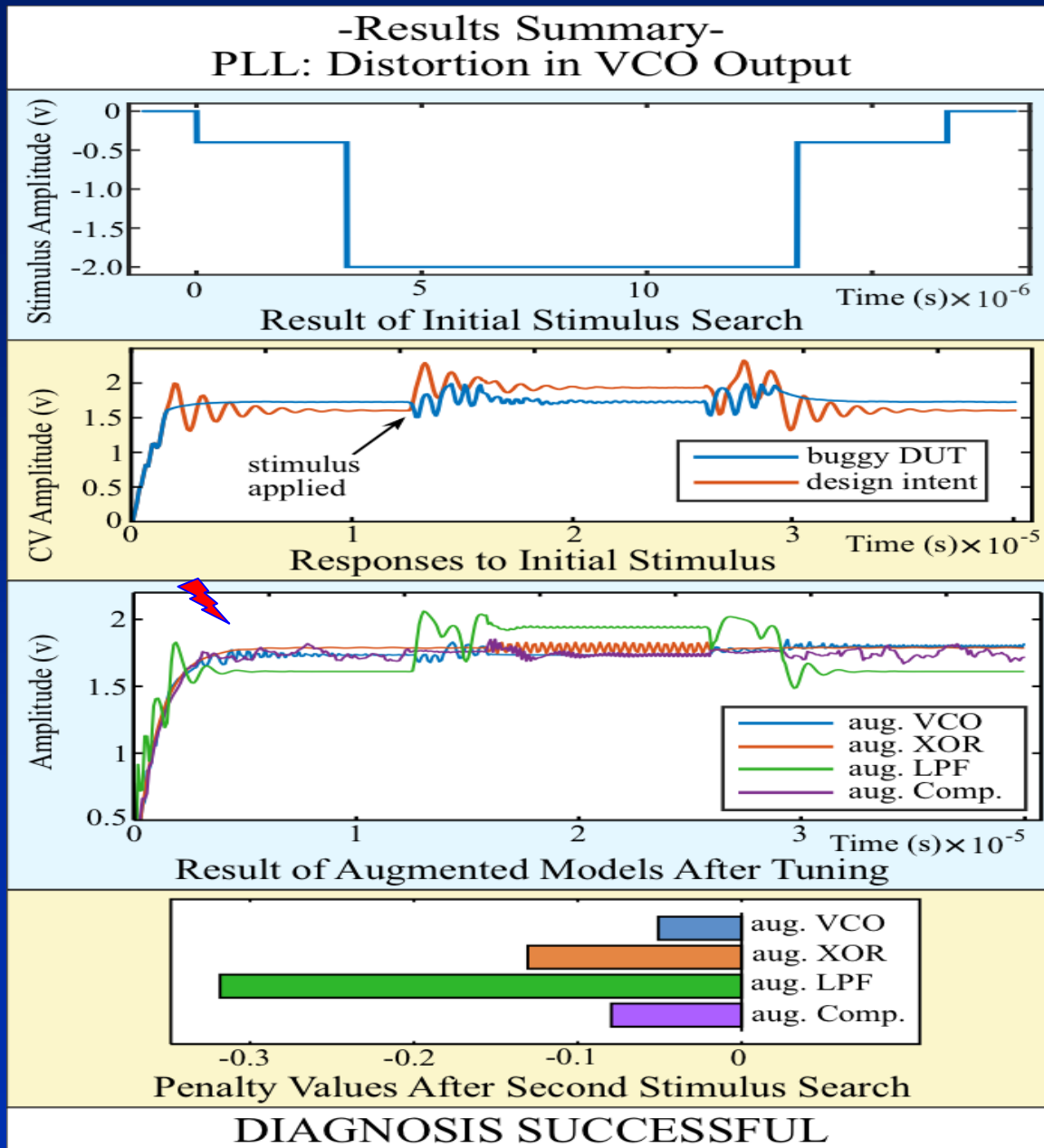


PLL Experiments



- System stimulated by summing LP signal at VCO input
- System observed immediately prior to summing

PLL Experiment: Buggy VCO Output



Questions ?

